

MT6808D1

N-Channel Power MOSFET

60V,80A,8.0mΩ

Features

- Typ $R_{DS(on)} = 8.0m\Omega$ at $V_{GS} = 10V, I_D = 20A$
- High performance trench technology for extremely low $R_{DS(on)}$
- High power and current handing capability

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

Applications

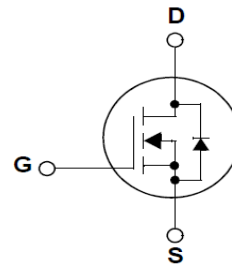
- DC-DC primary bridge
- DC-DC Synchronous rectification
- Power Management for Inverter Systems



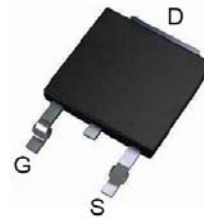
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Simplified Schematic



MARKING DIAGRAM & PIN ASSIGNMENT



TO-252-2L

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		± 20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _C =25°C		A

Mounted on Large Heat Sink

I _{DM}	Pulsed Drain Current *		180	A
I _D	Continuous Drain Current	T _C =25°C	80	A
		T _C =100°C	45	
P _D	Maximum Power Dissipation	T _C =25°C	50	W
		T _C =100°C	35	
R _{θJC}	Thermal Resistance-Junction to Case		1.3	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient		32.5	
Avalanche Ratings				
E _{AS}	Avalanche Energy, Single Pulsed	L=0.5mH	220***	mJ

Note : * Repetitive rating ; pulse width limited by junction temperature
 ** Drain current is limited by junction temperature
 *** VD=55V

Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

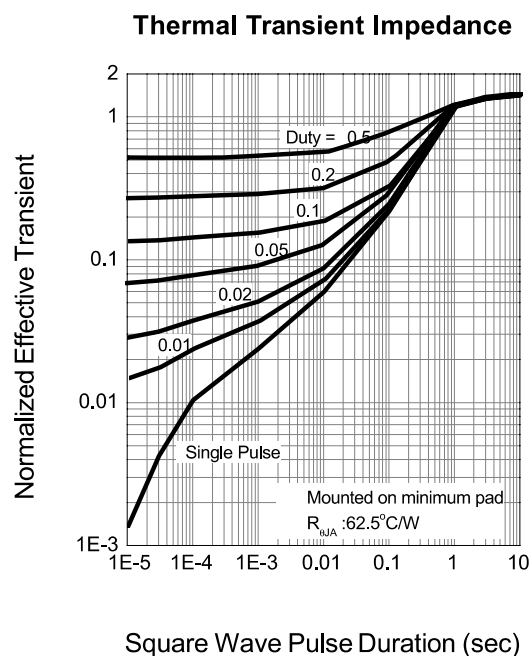
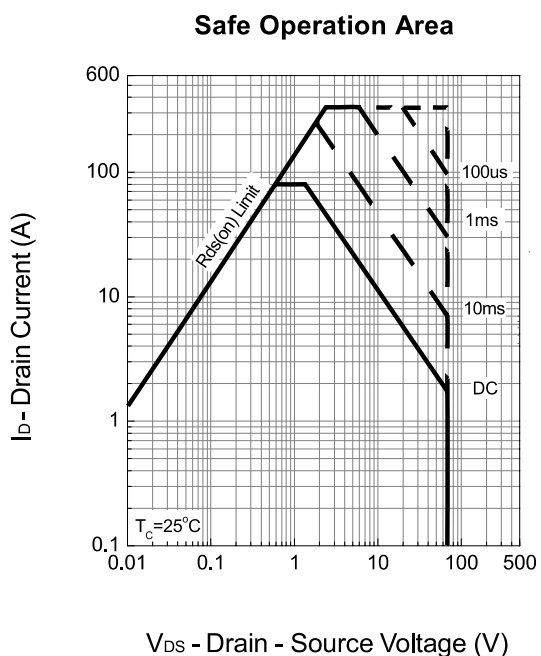
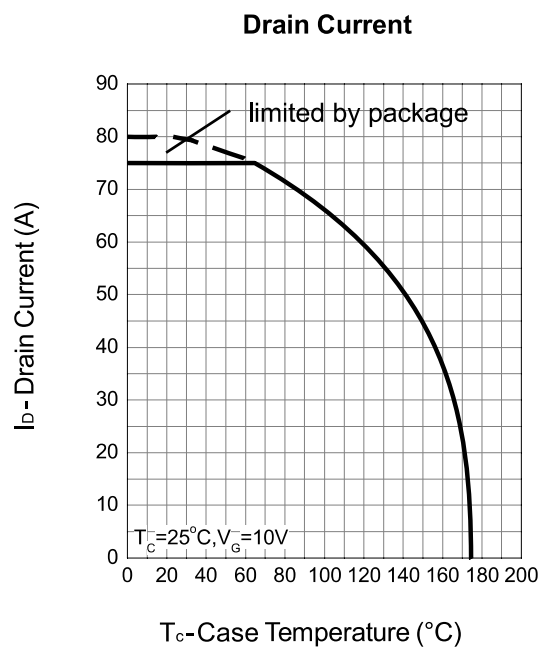
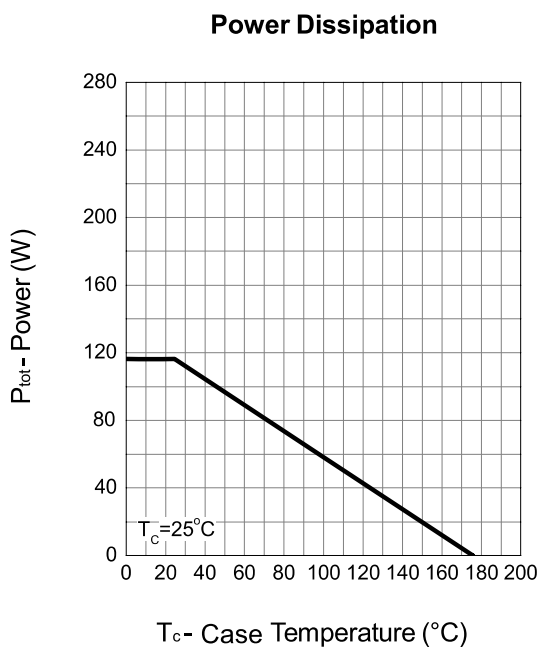
Symbol	Parameter	Test Conditions				Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	10	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	2.6	3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} *	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =40A	-	8.0	9.0	mΩ
Diode Characteristics						
V _{SD} *	Diode Forward Voltage	I _{SD} =40A, V _{GS} =0V	-	0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =40A, dI _{SD} /dt=100A/μs	-	33	-	ns
Q _{rr}	Reverse Recovery Charge		-	61	-	nC

Electrical Characteristics (Cont.) (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions				Unit
			Min.	Typ.	Max.	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.8	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, Frequency=1.0MHz	-	4400	-	pF
C _{oss}	Output Capacitance		-	210	-	
C _{rss}	Reverse Transfer Capacitance		-	190	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =34V, R _G =3 Ω, I _{DS} =40A, V _{GS} =10V,	-	15	-	ns
T _r	Turn-on Rise Time		-	13	-	
t _{d(OFF)}	Turn-off Delay Time		-	20	-	
T _f	Turn-off Fall Time		-	8	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =55V, V _{GS} =10V, I _{DS} =40A	-	77	-	nC
Q _{gs}	Gate-Source Charge		-	9	-	
Q _{gd}	Gate-Drain Charge		-	23	-	

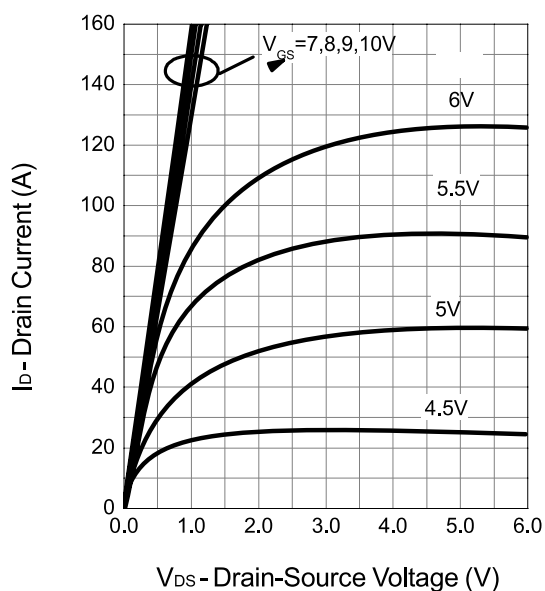
Note * : Pulse test ; pulse width ≤ 300μs, duty cycle ≤ 2%.

Typical Operating Characteristics

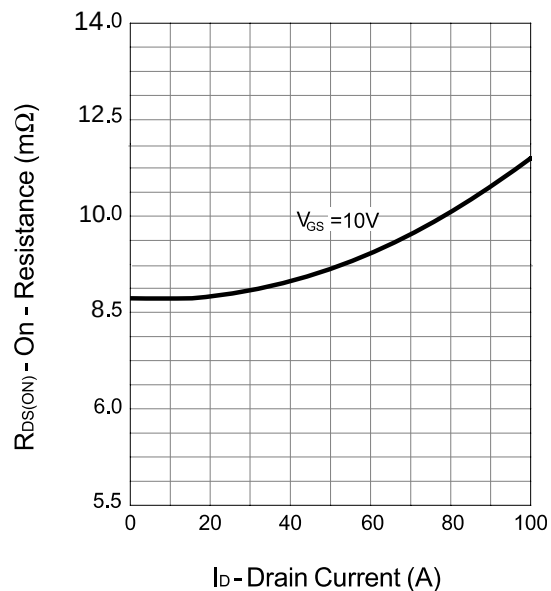


Typical Operating Characteristics (Cont.)

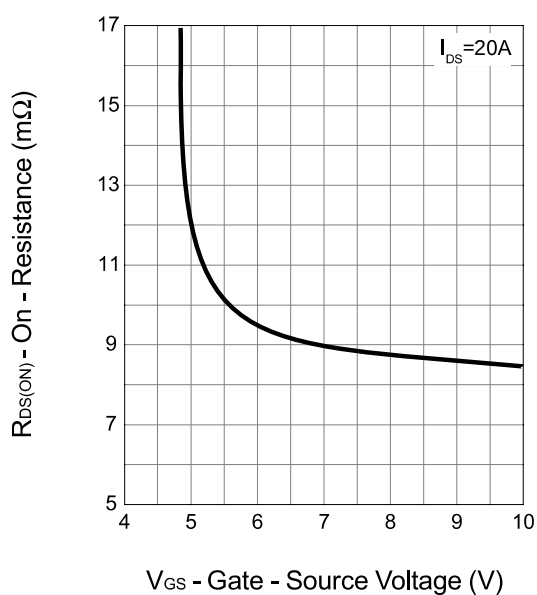
Output Characteristics



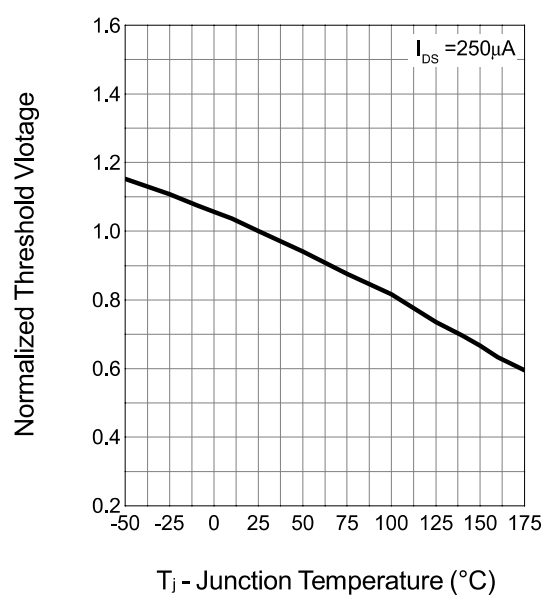
Drain-Source On Resistance



Drain-Source On Resistance

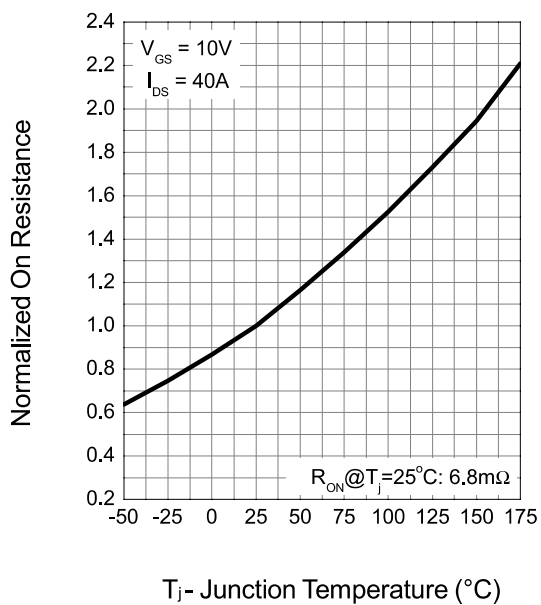


Gate Threshold Voltage

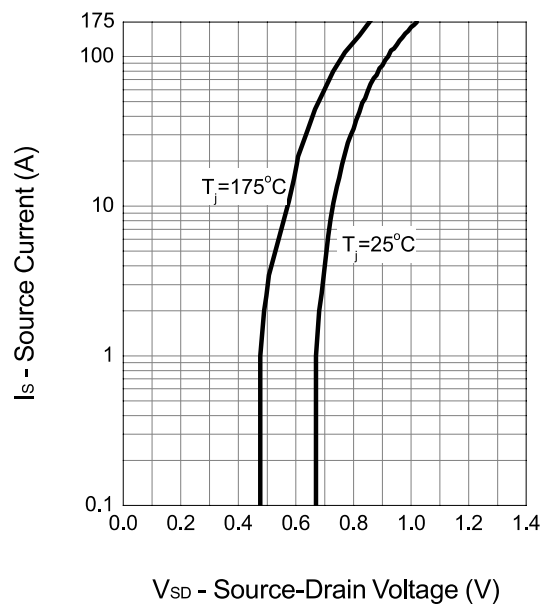


Typical Operating Characteristics (Cont.)

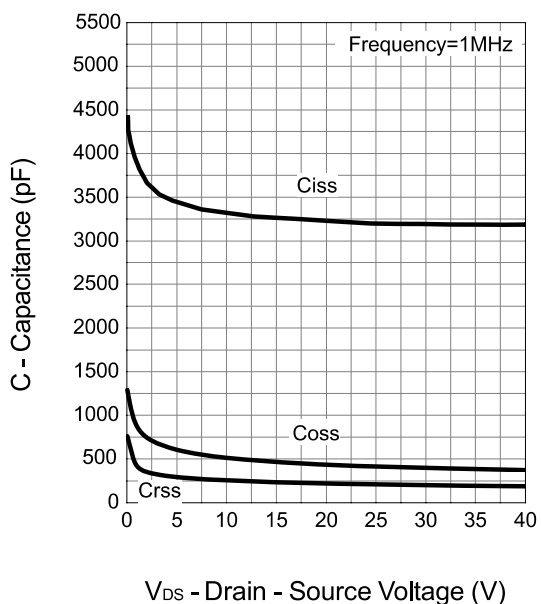
Drain-Source On Resistance



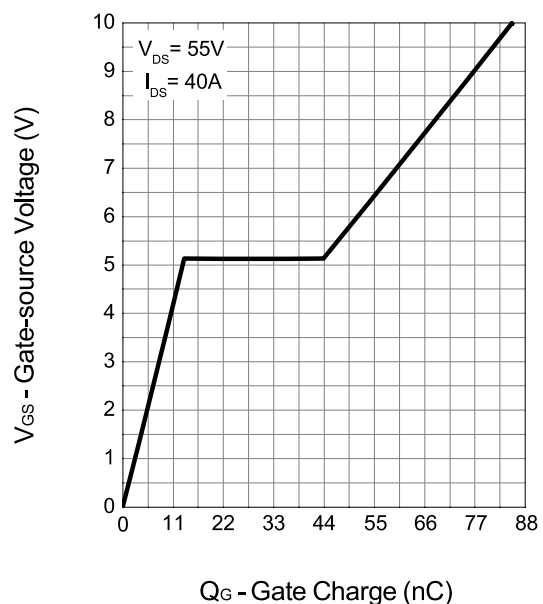
Source-Drain Diode Forward



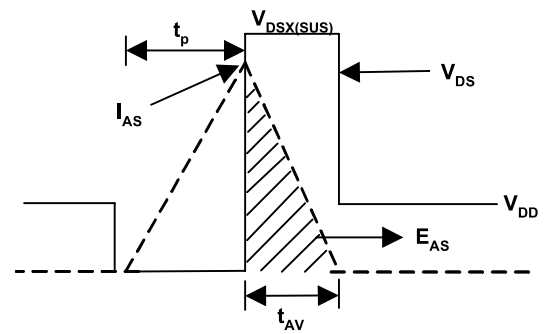
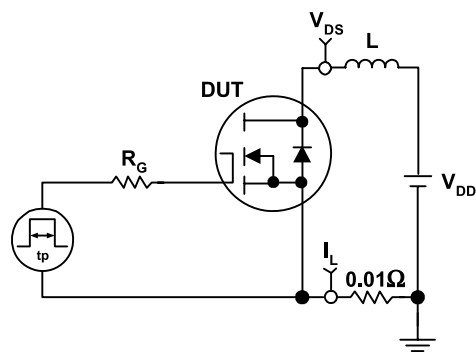
Capacitance



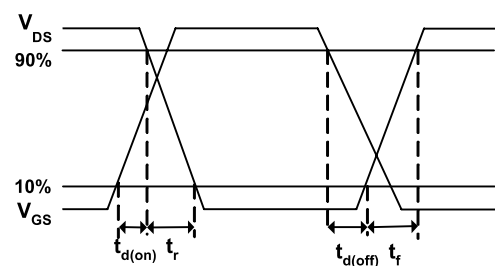
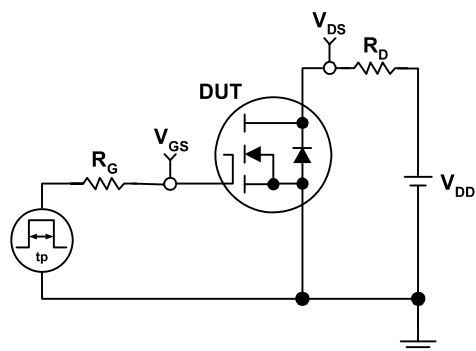
Gate Charge



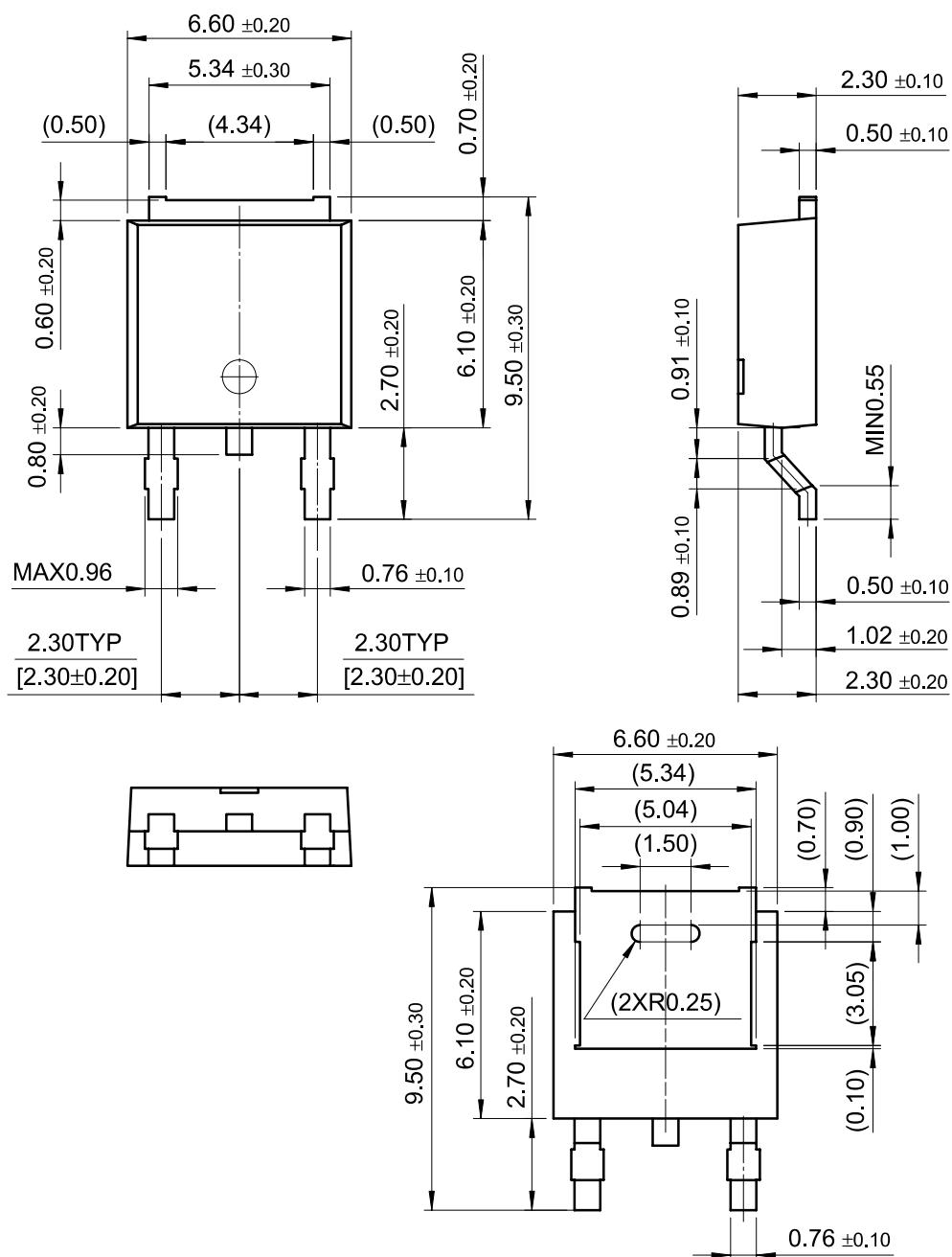
Avalanche Test Circuit and Waveforms



Avalanche Test Circuit and Waveforms



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